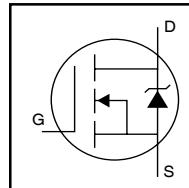


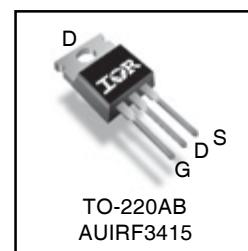
**Features**

- Advanced Planar Technology
- Low On-Resistance
- Dynamic dv/dt Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Repetitive Avalanche Allowed up to  $T_{jmax}$
- Lead-Free, RoHS Compliant
- Automotive Qualified\*

HEXFET® Power MOSFET



$V_{(BR)DSS}$	150V
$R_{DS(on)}$ max.	0.042Ω
$I_D$	43A



G	D	S
Gate	Drain	Source

**Description**

Specifically designed for Automotive applications, this cellular design of HEXFET® Power MOSFETs utilizes the latest processing techniques to achieve low on-resistance per silicon area. This benefit combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in Automotive and a wide variety of other applications.

**Absolute Maximum Ratings**

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature ( $T_A$ ) is 25°C, unless otherwise specified.

	Parameter	Max.	Units
$I_D$ @ $T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS}$ @ 10V	43	A
$I_D$ @ $T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS}$ @ 10V	30	
$I_{DM}$	Pulsed Drain Current ①	150	
$P_D$ @ $T_C = 25^\circ\text{C}$	Power Dissipation	200	W
	Linear Derating Factor	1.3	W/°C
$V_{GS}$	Gate-to-Source Voltage	± 20	V
$E_{AS}$	Single Pulse Avalanche Energy (Thermally Limited) ②	590	mJ
$I_{AR}$	Avalanche Current ①	22	A
$E_{AR}$	Repetitive Avalanche Energy ①	20	mJ
$dv/dt$	Peak Diode Recovery $dv/dt$ ③	5.0	V/ns
$T_J$	Operating Junction and	-55 to + 175	°C
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 seconds (1.6mm from case)		
	Mounting Torque, 6-32 or M3 screw	10 lbf·in (1.1N·m)	

**Thermal Resistance**

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ④	—	0.75	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient	—	62	

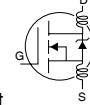
HEXFET® is a registered trademark of International Rectifier.

\*Qualification standards can be found at <http://www.irf.com/>

Static Electrical Characteristics @  $T_J = 25^\circ\text{C}$  (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(\text{BR})\text{DSS}}$	Drain-to-Source Breakdown Voltage	150	—	—	V	$V_{\text{GS}} = 0\text{V}$ , $I_D = 250\mu\text{A}$
$\Delta V_{(\text{BR})\text{DSS}}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.17	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}$ , $I_D = 1\text{mA}$
$R_{\text{DS}(\text{on})}$	Static Drain-to-Source On-Resistance	—	—	0.042	$\Omega$	$V_{\text{GS}} = 10\text{V}$ , $I_D = 22\text{A}$ ④
$V_{\text{GS}(\text{th})}$	Gate Threshold Voltage	2.0	—	4.0	V	$V_{\text{DS}} = V_{\text{GS}}$ , $I_D = 250\mu\text{A}$
$g_{\text{fs}}$	Forward Transconductance	19	—	—	S	$V_{\text{DS}} = 50\text{V}$ , $I_D = 22\text{A}$
$I_{\text{DSS}}$	Drain-to-Source Leakage Current	—	—	25	$\mu\text{A}$	$V_{\text{DS}} = 150\text{V}$ , $V_{\text{GS}} = 0\text{V}$
		—	—	250		$V_{\text{DS}} = 120\text{V}$ , $V_{\text{GS}} = 0\text{V}$ , $T_J = 150^\circ\text{C}$
$I_{\text{GSS}}$	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{\text{GS}} = 20\text{V}$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{\text{GS}} = -20\text{V}$

Dynamic Electrical Characteristics @  $T_J = 25^\circ\text{C}$  (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$Q_g$	Total Gate Charge	—	—	200	nC	$I_D = 22\text{A}$
$Q_{\text{gs}}$	Gate-to-Source Charge	—	—	17		$V_{\text{DS}} = 120\text{V}$
$Q_{\text{gd}}$	Gate-to-Drain ("Miller") Charge	—	—	98		$V_{\text{GS}} = 10\text{V}$ , See Fig. 6 & 13 ④
$t_{\text{d}(\text{on})}$	Turn-On Delay Time	—	12	—	ns	$V_{\text{DD}} = 75\text{V}$
$t_r$	Rise Time	—	55	—		$I_D = 22\text{A}$
$t_{\text{d}(\text{off})}$	Turn-Off Delay Time	—	71	—		$R_G = 2.5\ \Omega$
$t_f$	Fall Time	—	69	—		$R_D = 3.3\ \Omega$ , See Fig. 10
$L_D$	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
$L_S$	Internal Source Inductance	—	7.5	—		
$C_{\text{iss}}$	Input Capacitance	—	2400	—	pF	$V_{\text{GS}} = 0\text{V}$
$C_{\text{oss}}$	Output Capacitance	—	640	—		$V_{\text{DS}} = 25\text{V}$
$C_{\text{rss}}$	Reverse Transfer Capacitance	—	340	—		$f = 1.0\text{MHz}$ , See Fig. 5

## Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	43	A	MOSFET symbol showing the integral reverse p-n junction diode.
$I_{\text{SM}}$	Pulsed Source Current (Body Diode) ①	—	—	150		
$V_{\text{SD}}$	Diode Forward Voltage	—	—	1.3		$T_J = 25^\circ\text{C}$ , $I_S = 22\text{A}$ , $V_{\text{GS}} = 0\text{V}$ ④
$t_{\text{rr}}$	Reverse Recovery Time	—	260	390	ns	$T_J = 25^\circ\text{C}$ , $I_F = 22\text{A}$
$Q_{\text{rr}}$	Reverse Recovery Charge	—	2.2	3.3	nC	$\text{di}/\text{dt} = 100\text{A}/\mu\text{s}$ ④
$t_{\text{on}}$	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $LS+LD$ )				

## Notes:

① Repetitive rating; pulse width limited by max. junction temperature. ( See fig. 11 )  
 ②  $V_{\text{DD}} = 25\text{V}$ , starting  $T_J = 25^\circ\text{C}$ ,  $L = 2.4\text{mH}$   
 $R_G = 25\Omega$ ,  $I_{\text{AS}} = 22\text{A}$ . ( See Figure 12 )

③  $I_{\text{SD}} \leq 22\text{A}$ ,  $\text{di}/\text{dt} \leq 820\text{A}/\mu\text{s}$ ,  $V_{\text{DD}} \leq V_{(\text{BR})\text{DSS}}$ ,  
 $T_J \leq 175^\circ\text{C}$

④ Pulse width  $\leq 300\mu\text{s}$ ; duty cycle  $\leq 2\%$ .

⑤  $R_\theta$  is measured at  $T_J$  approximately  $90^\circ\text{C}$ .

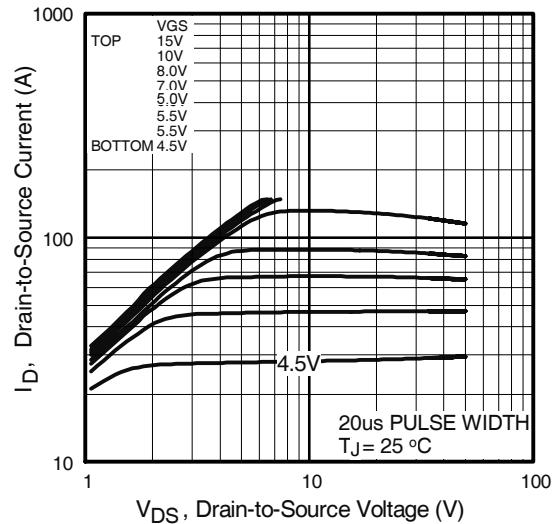
**Qualification Information<sup>†</sup>**

<b>Qualification Level</b>		Automotive (per AEC-Q101) <sup>††</sup>	
		Comments: This part number(s) passed Automotive qualification. IR's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.	
<b>Moisture Sensitivity Level</b>		TO-220	N/A
<b>ESD</b>	Machine Model	Class M4 (+/- 800V) <sup>†††</sup> AEC-Q101-002	
	Human Body Model	Class H2 (+/- 3500V) <sup>†††</sup> AEC-Q101-001	
	Charged Device Model	Class C5 (+/- 2000V) <sup>†††</sup> AEC-Q101-005	
<b>RoHS Compliant</b>		Yes	

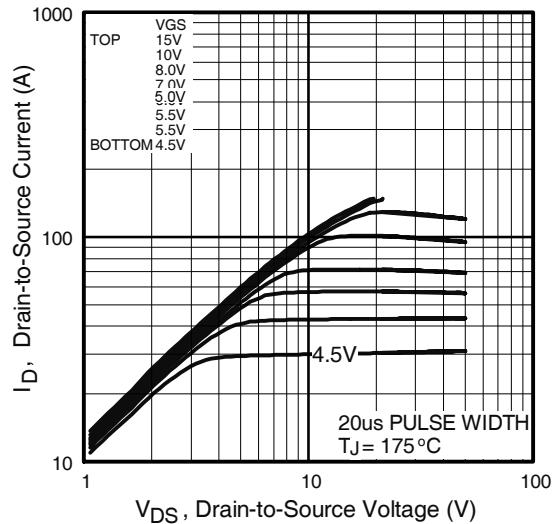
<sup>†</sup> Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/>

<sup>††</sup> Exceptions to AEC-Q101 requirements are noted in the qualification report.

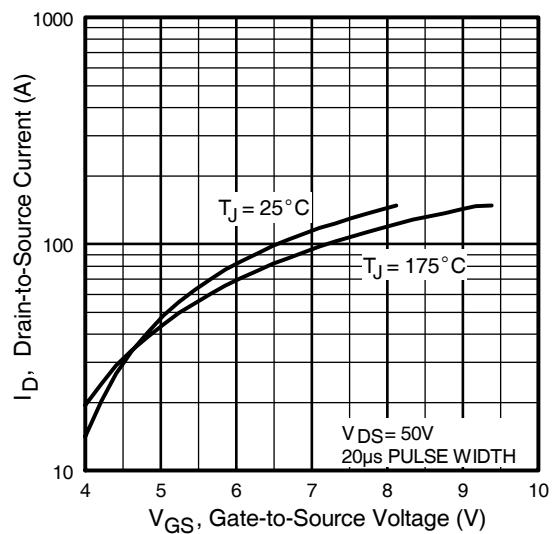
<sup>†††</sup> Highest passing voltage.



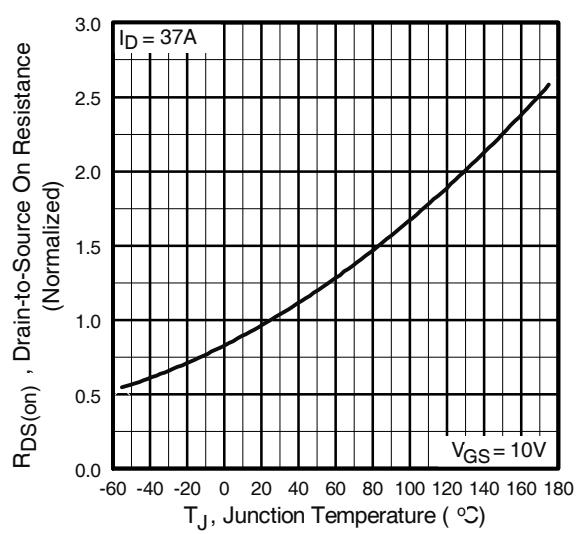
**Fig 1.** Typical Output Characteristics



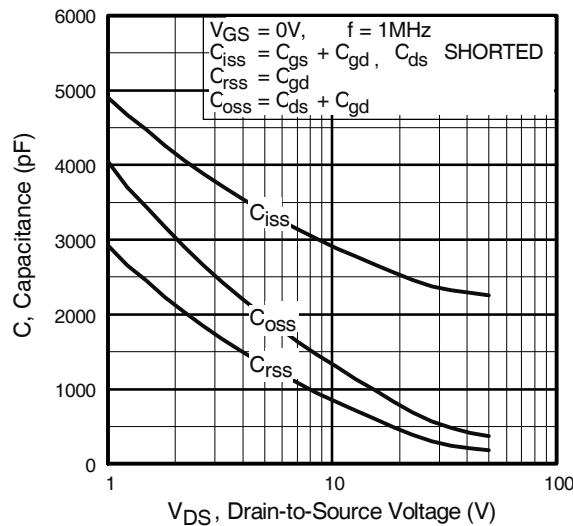
**Fig 2.** Typical Output Characteristics



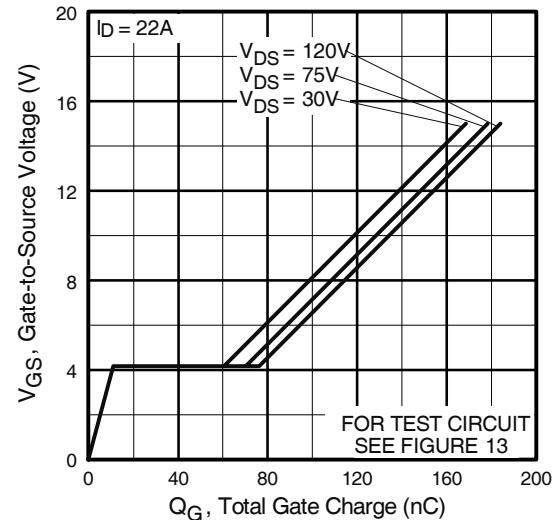
**Fig 3.** Typical Transfer Characteristics



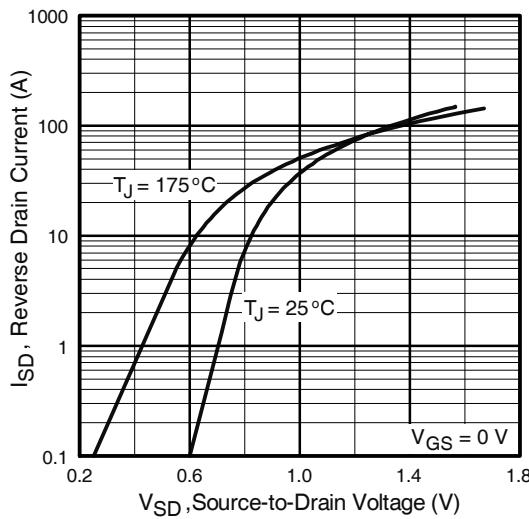
**Fig 4.** Normalized On-Resistance  
 Vs. Temperature



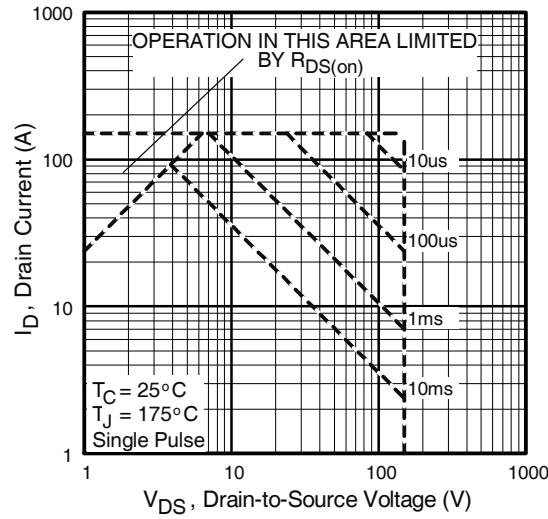
**Fig 5.** Typical Capacitance Vs.  
Drain-to-Source Voltage



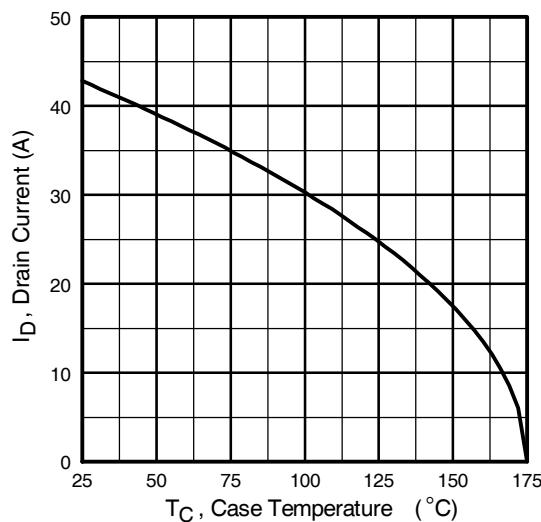
**Fig 6.** Typical Gate Charge Vs.  
Gate-to-Source Voltage



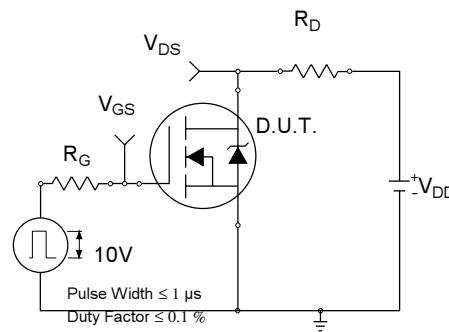
**Fig 7.** Typical Source-Drain Diode  
Forward Voltage



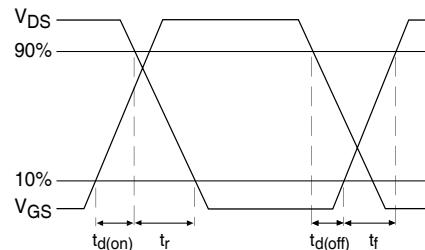
**Fig 8.** Maximum Safe Operating Area



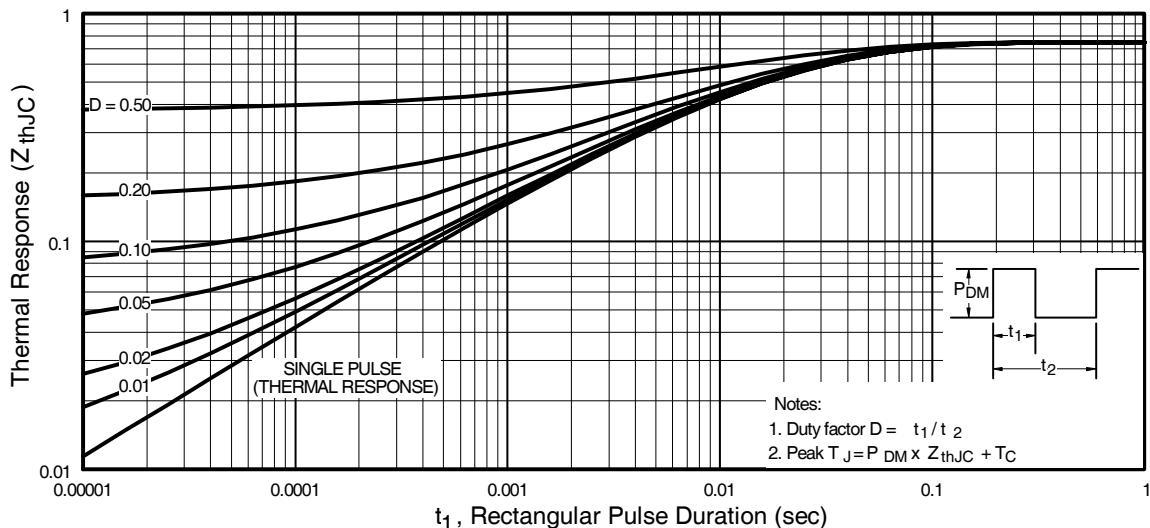
**Fig 9.** Maximum Drain Current Vs.  
Case Temperature



**Fig 10a.** Switching Time Test Circuit



**Fig 10b.** Switching Time Waveforms



**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case

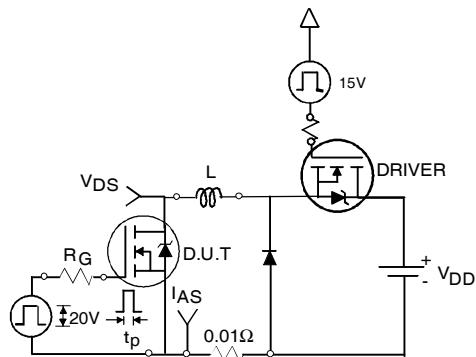


Fig 12a. Unclamped Inductive Test Circuit

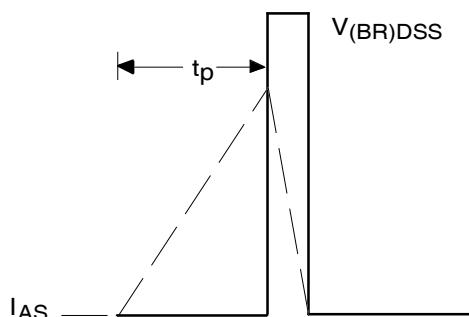
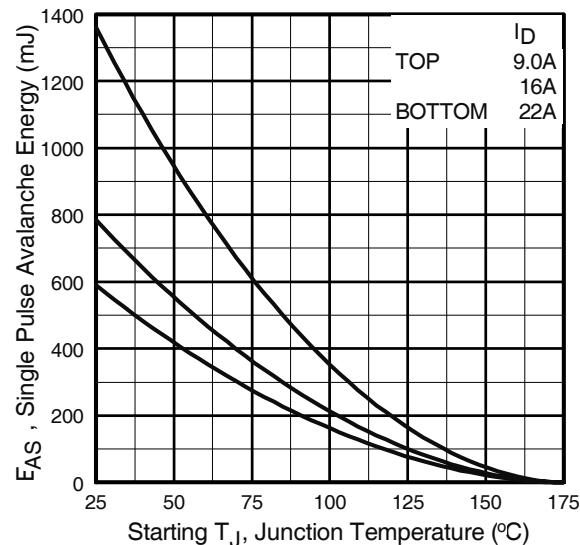


Fig 12b. Unclamped Inductive Waveforms

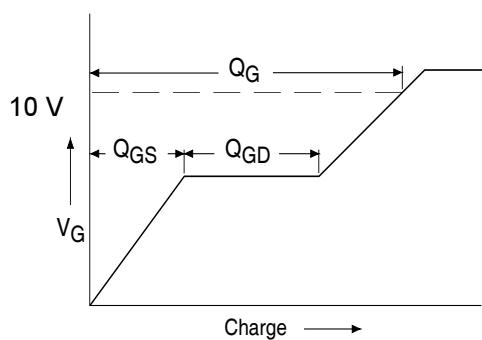


Fig 13a. Basic Gate Charge Waveform

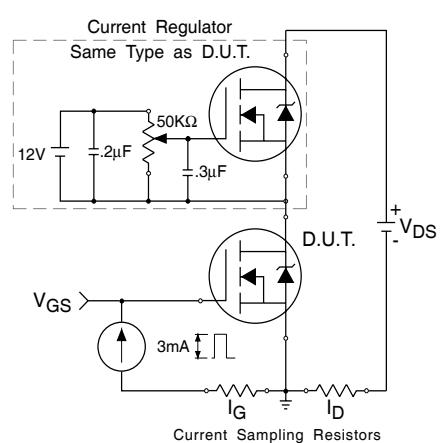
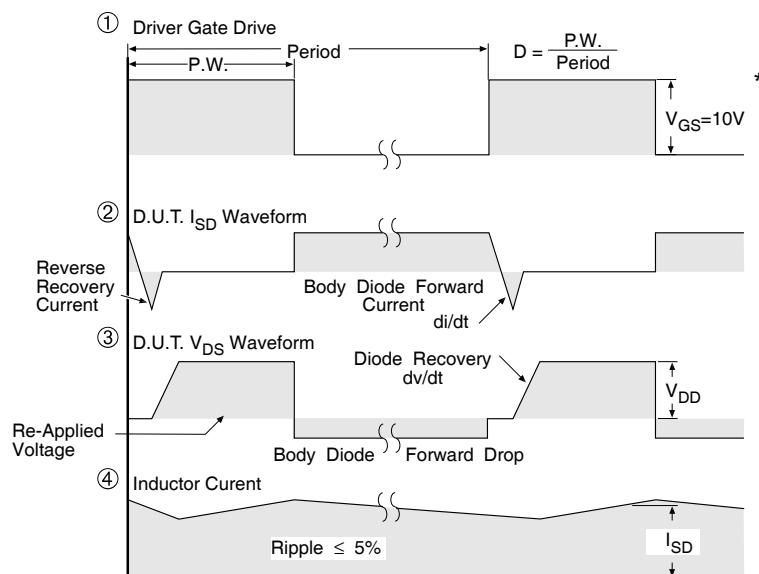
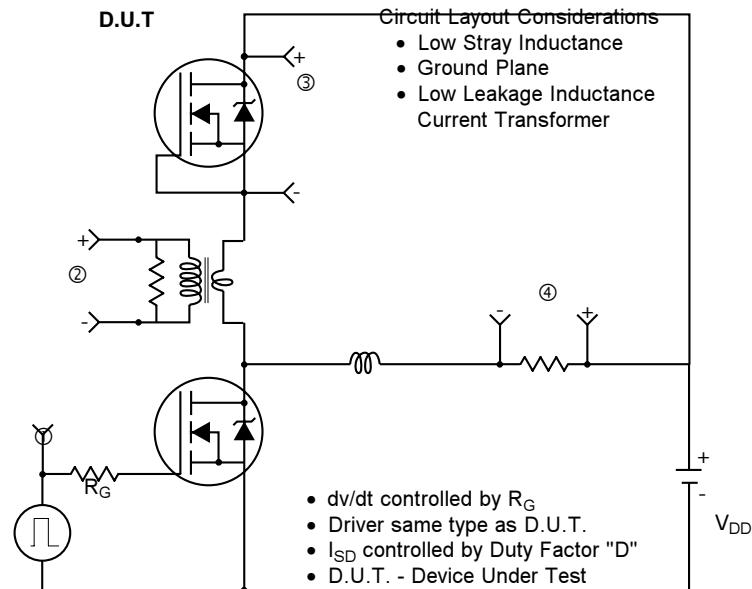


Fig 13b. Gate Charge Test Circuit

## Peak Diode Recovery dv/dt Test Circuit

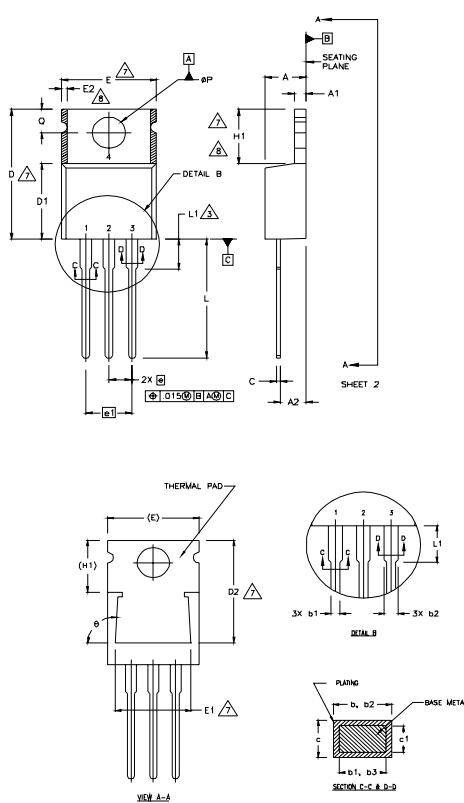


\*  $V_{GS} = 5V$  for Logic Level Devices

Fig 14. For N-Channel HEXFETS

## TO-220AB Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
2. DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS].
3. LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.
4. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5. DIMENSION b1 & c1 APPLY TO BASE METAL ONLY.
6. CONTROLLING DIMENSION : INCHES.
7. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS E,H1,D2 & E1
8. DIMENSION E2 X H1 DEFINE A ZONE WHERE STAMPING AND SINGULATION IRRREGULARITIES ARE ALLOWED.

LEAD ASSIGNMENTS

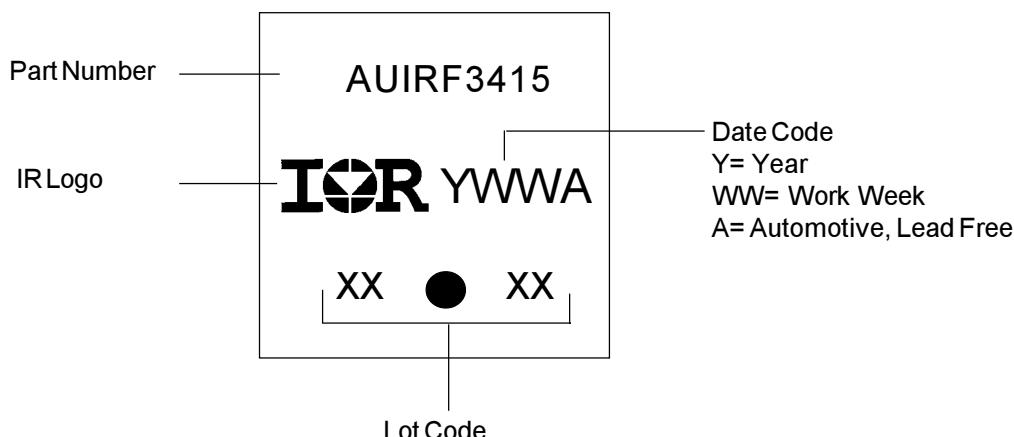
HEXFET  
1.- GATE  
2.- DRAIN  
3.- SOURCE

IGBTs, CoPACK  
1.- GATE  
2.- COLLECTOR  
3.- Emitter

DIODES  
1.- ANODE/OPEN  
2.- CATHODE  
3.- ANODE

SYMBOL	DIMENSIONS				NOTES	
	MILLIMETERS		INCHES			
	MIN.	MAX.	MIN.	MAX.		
A	3.56	4.82	.140	.190		
A1	0.51	1.40	.020	.055		
A2	2.04	2.92	.080	.115		
b	0.38	1.01	.015	.040		
b1	0.38	0.96	.015	.038	5	
b2	1.15	1.77	.045	.070		
b3	1.15	1.73	.045	.068		
c	0.36	0.61	.014	.024		
c1	0.36	0.56	.014	.022	5	
D	14.22	16.51	.560	.650	4	
D1	8.38	9.02	.330	.355		
D2	12.19	12.88	.480	.507	7	
E	9.66	10.66	.380	.420	4,7	
E1	8.38	8.89	.330	.350	7	
e	2.54	BSC	.100	BSC		
e1	5.08		.200	BSC		
H1	5.85	6.55	.230	.270	7,8	
L	12.70	14.73	.500	.580		
L1	—	6.35	—	.250	3	
ØP	3.54	4.08	.139	.161		
O	2.54	3.42	.100	.135		
Ø	90°-93°		90°-93°			

## TO-220AB Part Marking Information



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

## Ordering Information

Base part number	Package Type	Standard Pack		Complete Part Number
		Form	Quantity	
AUIRF3415	TO-220	Tube	50	AUIRF3415

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